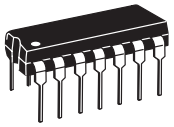
8-Bit Serial-Input/ Parallel-Output Shift Register

High–Performance Silicon–Gate CMOS

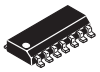
The 74HC164A is identical in pinout to the LS164. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

The MC74HC164A is an 8–bit, serial–input to parallel–output shift register. Two serial data inputs, A1 and A2, are provided so that one input may be used as a data enable. Data is entered on each rising edge of the clock. The active–low asynchronous Reset overrides the Clock and Serial Data inputs.

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2 to 6 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 244 FETs or 61 Equivalent Gates

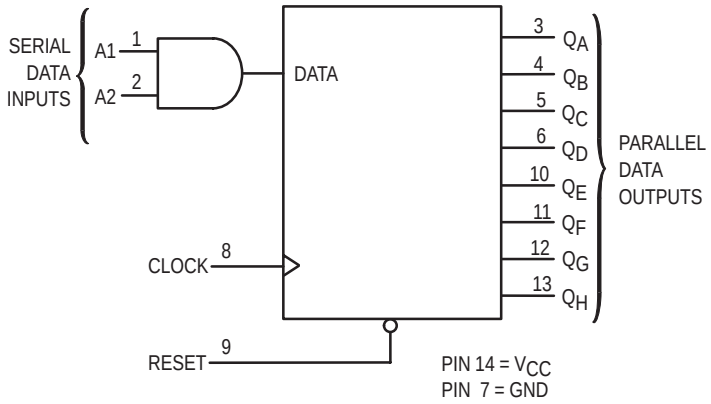


DIP–14
N SUFFIX
CASE 646

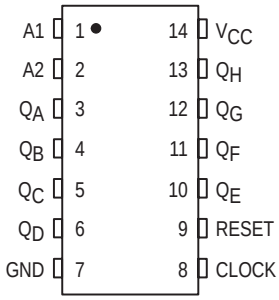


SOP–14
D SUFFIX
CASE 751A

LOGIC DIAGRAM



PIN ASSIGNMENT



FUNCTION TABLE

Inputs				Outputs			
Reset	Clock	A1	A2	Q_A	Q_B	…	Q_H
L	X	X	X	L	L	…	L
H	↘	X	X	No Change			
H	↗	H	D	D	Q_{An}	…	Q_{Gn}
H	↗	D	H	D	Q_{An}	…	Q_{Gn}

D = data input
Q_{An} – Q_{Gn} = data shifted from the preceding stage on a rising edge at the clock input.

ORDERING INFORMATION

Device	Package	Shipping
74HC164N	DIP–14	2000 / Box
74HC164M/TR	SOP–14	2500 / Reel

MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	– 0.5 to + 7.0	V
V_{in}	DC Input Voltage (Referenced to GND)	– 0.5 to V_{CC} + 0.5	V
V_{out}	DC Output Voltage (Referenced to GND)	– 0.5 to V_{CC} + 0.5	V
I_{in}	DC Input Current, per Pin	± 20	mA
I_{out}	DC Output Current, per Pin	± 25	mA
I_{CC}	DC Supply Current, V_{CC} and GND Pins	± 50	mA
P_D	Power Dissipation in Still Air, Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T_{stg}	Storage Temperature	– 65 to + 150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP, SOIC or TSSOP Package)	260	°C

*Maximum Ratings are those values beyond which damage to the device may occur.
Functional operation should be restricted to the Recommended Operating Conditions.
†Derating — Plastic DIP: – 10 mW/°C from 65° to 125°C
SOIC Package: – 7 mW/°C from 65° to 125°C
TSSOP Package: – 6.1 mW/°C from 65° to 125°C
For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND ≤ (V_{in} or V_{out}) ≤ V_{CC}.
Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	2.0	6.0	V
V_{in}, V_{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V_{CC}	V
T_A	Operating Temperature, All Package Types	– 55	+ 125	°C
t_r, t_f	Input Rise and Fall Time (Figure 1) V_{CC} = 2.0 V V_{CC} = 4.5 V V_{CC} = 6.0 V	0 0 0	1000 500 400	ns

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V_{CC} V	Guaranteed Limit –55°C to 25°C	Guaranteed Limit ≤ 85°C	Guaranteed Limit ≤ 125°C	Unit
V_{IH}	Minimum High–Level Input Voltage	V_{out} = 0.1 V or V_{CC} – 0.1 V $\|I_{out}\|$ ≤ 20 μA	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	V
V_{IL}	Maximum Low–Level Input Voltage	V_{out} = 0.1 V or V_{CC} – 0.1 V $\|I_{out}\|$ ≤ 20 μA	2.0 3.0 4.5 6.0	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	V
V_{OH}	Minimum High–Level Output Voltage	V_{in} = V_{IH} or V_{IL} $\|I_{out}\|$ ≤ 20 μA	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		V_{in} = V_{IH} or V_{IL} $\|I_{out}\|$ ≤ 2.4 mA $\|I_{out}\|$ ≤ 4.0 mA $\|I_{out}\|$ ≤ 5.2 mA	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.20 3.70 5.20	

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V_{CC} V	Guaranteed Limit			Unit
				–55°C to 25°C	≤ 85°C	≤ 125°C	
V_{OL}	Maximum Low–Level Output Voltage	$V_{in} = V_{IH}$ or V_{IL} $\|I_{out}\| \leq 20$ μA	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$V_{in} = V_{IH}$ or V_{IL} $\|I_{out}\| \leq 2.4$ mA $\|I_{out}\| \leq 4.0$ mA $\|I_{out}\| \leq 5.2$ mA	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.40 0.40 0.40	
I_{in}	Maximum Input Leakage Current	$V_{in} = V_{CC}$ or GND	6.0	± 0.1	± 1.0	± 1.0	μA
I_{CC}	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0$ μA	6.0	4	40	160	μA

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

AC ELECTRICAL CHARACTERISTICS ($C_L = 50$ pF, Input $t_r = t_f = 6$ ns)

Symbol	Parameter	V_{CC} V	Guaranteed Limit			Unit
			–55°C to 25°C	≤ 85°C	≤ 125°C	
f_{max}	Maximum Clock Frequency (50% Duty Cycle) (Figures 1 and 4)	2.0 3.0 4.5 6.0	10 20 40 50	10 20 35 45	10 20 30 40	MHz
t_{PLH}, t_{PHL}	Maximum Propagation Delay, Clock to Q (Figures 1 and 4)	2.0 3.0 4.5 6.0	160 100 32 27	200 150 40 34	250 200 48 42	ns
t_{PHL}	Maximum Propagation Delay, Reset to Q (Figures 2 and 4)	2.0 3.0 4.5 6.0	175 100 35 30	220 150 44 37	260 200 53 45	ns
t_{TLH}, t_{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 4)	2.0 3.0 4.5 6.0	75 27 15 13	95 32 19 16	110 36 22 19	ns
C_{in}	Maximum Input Capacitance	—	10	10	10	pF

NOTES:
1. For propagation delays with loads other than 50 pF, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).
2. Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, $V_{CC} = 5.0$ V	
C_{PD}	Power Dissipation Capacitance (Per Package)*	180	pF

* Used to determine the no–load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$. For load considerations, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

TIMING REQUIREMENTS (Input $t_r = t_f = 6$ ns)

Symbol	Parameter	V_{CC} V	Guaranteed Limit			Unit
			−55°C to 25°C	≤ 85°C	≤ 125°C	
t_{su}	Minimum Setup Time, A1 or A2 to Clock (Figure 3)	2.0 3.0 4.5 6.0	25 15 7 5	35 20 8 6	40 25 9 6	ns
t_h	Minimum Hold Time, Clock to A1 or A2 (Figure 3)	2.0 3.0 4.5 6.0	3 3 3 3	3 3 3 3	3 3 3 3	ns
t_{rec}	Minimum Recovery Time, Reset Inactive to Clock (Figure 2)	2.0 3.0 4.5 6.0	3 3 3 3	3 3 3 3	3 3 3 3	ns
t_w	Minimum Pulse Width, Clock (Figure 1)	2.0 3.0 4.5 6.0	50 26 12 10	60 35 15 12	75 45 20 15	ns
t_w	Minimum Pulse Width, Reset (Figure 2)	2.0 3.0 4.5 6.0	50 26 12 10	60 35 15 12	75 45 20 15	ns
t_r, t_f	Maximum Input Rise and Fall Times (Figure 1)	2.0 3.0 4.5 6.0	1000 800 500 400	1000 800 500 400	1000 800 500 400	ns

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

PIN DESCRIPTIONS

INPUTS

A1, A2 (Pins 1, 2)

Serial Data Inputs. Data at these inputs determine the data to be entered into the first stage of the shift register. For a high level to be entered into the shift register, both A1 and A2 inputs must be high, thereby allowing one input to be used as a data–enable input. When only one serial input is used, the other must be connected to V_{CC}.

Clock (Pin 8)

Shift Register Clock. A positive–going transition on this pin shifts the data at each stage to the next stage. The shift register is completely static, allowing clock rates down to DC in a continuous or intermittent mode.

OUTPUTS

Q_A – Q_H (Pins 3, 4, 5, 6, 10, 11, 12, 13)

Parallel Shift Register Outputs. The shifted data is presented at these outputs in true, or noninverted, form.

CONTROL INPUT

Reset (Pin 9)

Active–Low, Asynchronous Reset Input. A low voltage applied to this input resets all internal flip–flops and sets Outputs Q_A – Q_H to the low level state.

SWITCHING WAVEFORMS

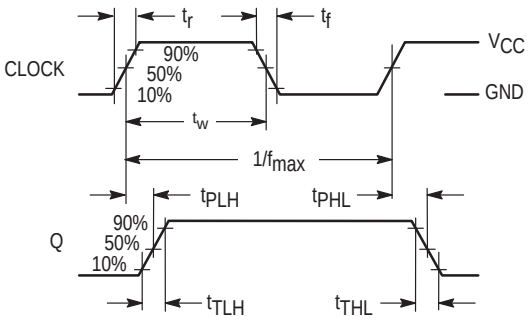


Figure 1.

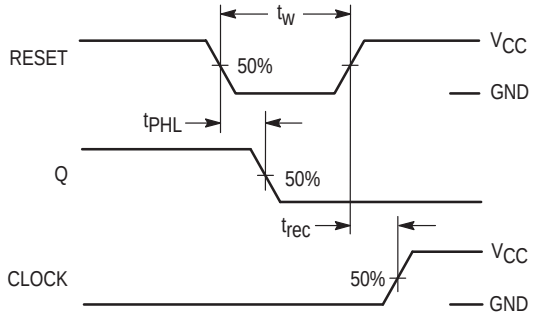


Figure 2.

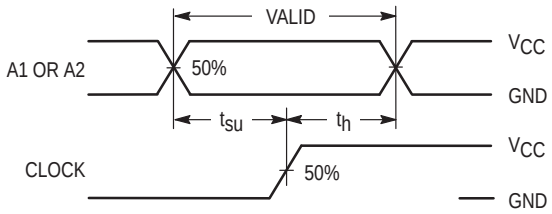
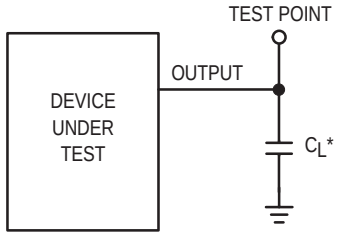


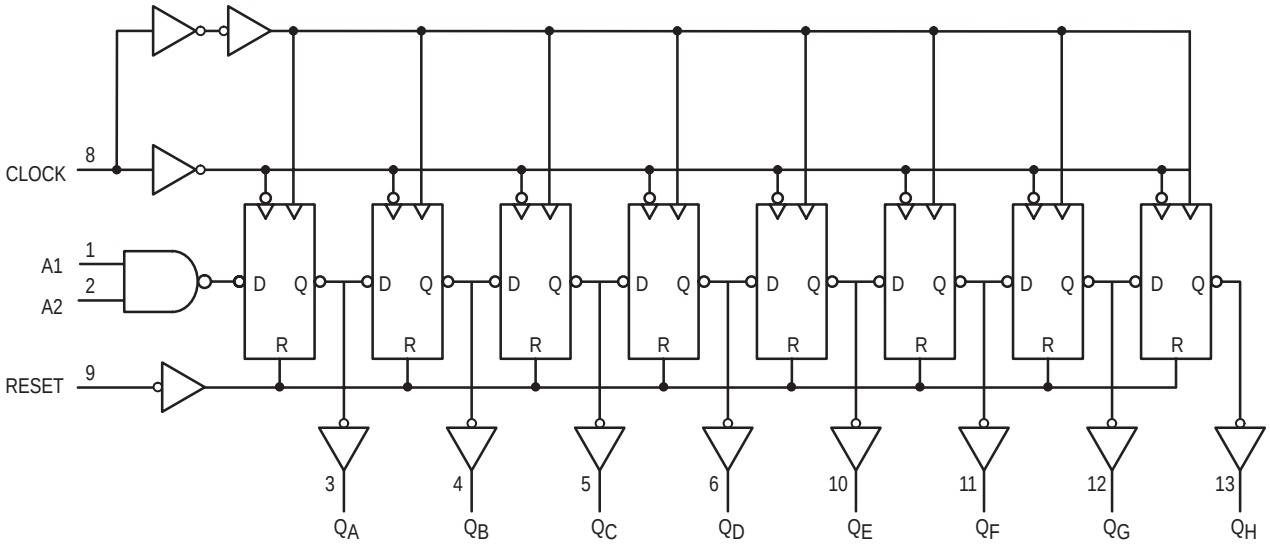
Figure 3.



*Includes all probe and jig capacitance

Figure 4. Test Circuit

EXPANDED LOGIC DIAGRAM



TIMING DIAGRAM